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June 2014

## **FQA27N25**

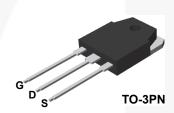
# N-Channel QFET® MOSFET 250 V, 27 A, 110 mΩ

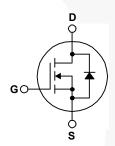
### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### **Features**

- 27 A, 250 V,  $R_{DS(on)}$  = 110 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 13.5 A
- Low Gate Charge (Typ. 50nC)
- · Low Crss( Typ. 45pF)
- 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQA27N25	Unit
V <sub>DSS</sub>	Drain-Source Voltage		250	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C	:)	27	А
	- Continuous (T <sub>C</sub> = 100°	C)	17	A
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	108	A
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	600	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	27	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	21	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		210	W
	- Derate above 25°C		1.67	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

### **Thermal Characteristics**

Symbol	Parameter	FQA27N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case , Max.	0.6	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink , Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient , Max.	40	°C/W

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA27N25	FQA27N25	TO-3PN	Tube	N/A	N/A	30 units

### Electrical Characteristics T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	250			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.29		V/°C
I <sub>DSS</sub>	Zero Onto William Busin Orange	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 13.5 A		0.083	0.11	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 13.5 A		25		S
	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1900	2450	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		360	470	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			45	60	pF
Switchi	ng Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 27 A,		32	75	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		270	550	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			80	170	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		120	250	ns
Qg	Total Gate Charge	$V_{DS} = 200 \text{ V}, I_{D} = 27 \text{ A},$		50	65	nC
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = 10 V		12.5	-	nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)	/	26	1	nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				27	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				108	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 27 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 27 A, 2		220	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		1.8	//	μС

- **Notes:** 1. Sepetitive Rating: Pulse width limited by maximum junction temperature 2. L = 1.3 mH,  $I_{AS}$  = 27 A,  $V_{DD}$  = 50 V,  $R_G$  = 25  $\Omega$ , Starting  $T_J$  = 25°C 3.  $I_{SD} \le 27$  A, di/dt  $\le 300$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , Starting  $T_J$  = 25°C 4. Essentially independent of operating temperature

### **Typical Characteristics**

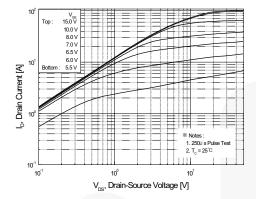


Figure 1. On-Region Characteristics

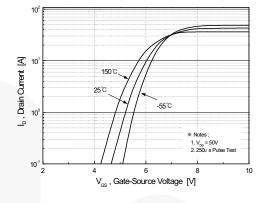


Figure 2. Transfer Characteristics

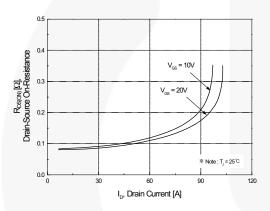


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

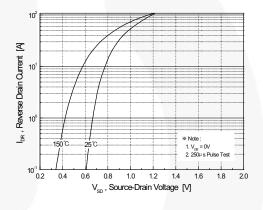


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

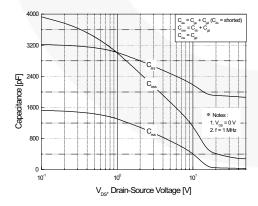


Figure 5. Capacitance Characteristics

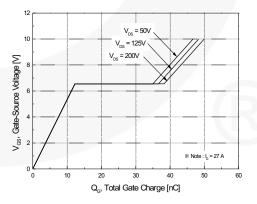


Figure 6. Gate Charge Characteristics

### Typical Characteristics (Continued)

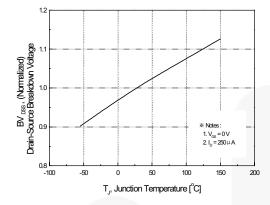


Figure 7. Breakdown Voltage Variation vs. Temperature

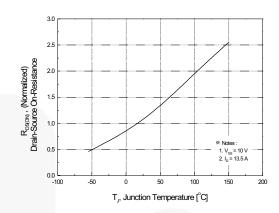


Figure 8. On-Resistance Variation vs. Temperature

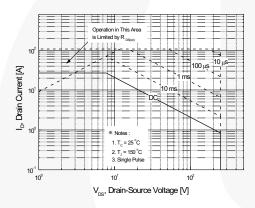


Figure 9. Maximum Safe Operating Area

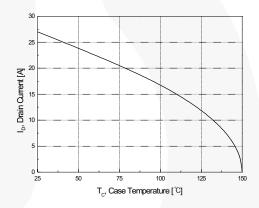


Figure 10. Maximum Drain Current vs. Case Temperature

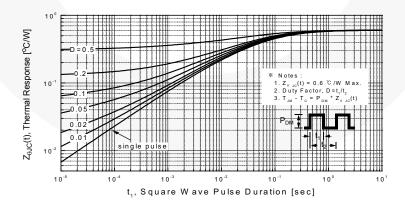


Figure 11. Transient Thermal Response Curve

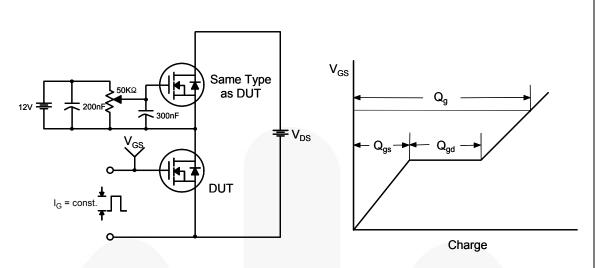


Figure 12. Gate Charge Test Circuit & Waveform

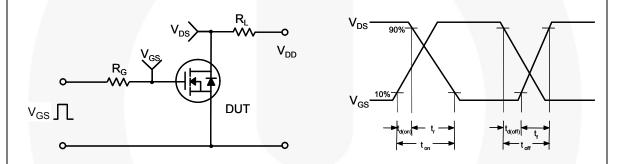


Figure 13. Resistive Switching Test Circuit & Waveforms

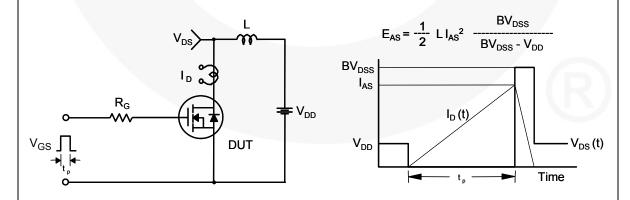
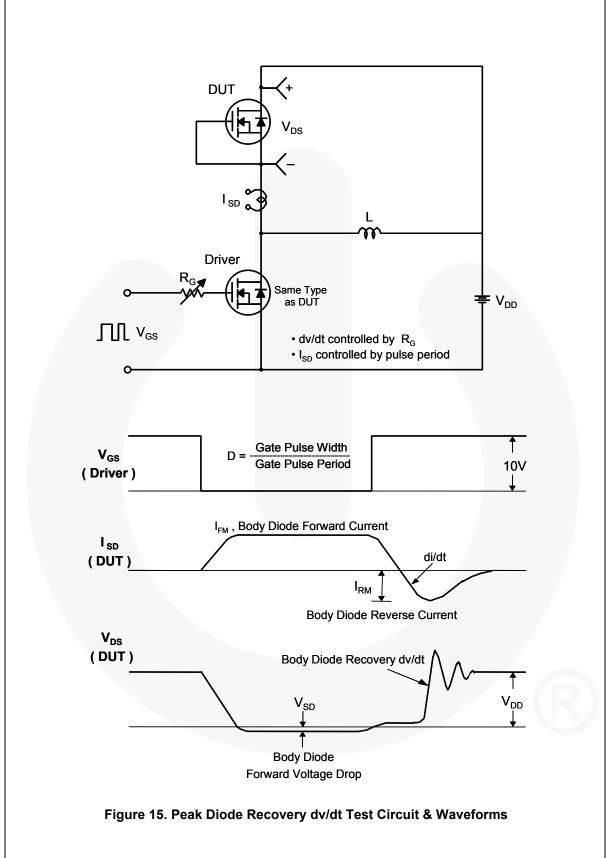
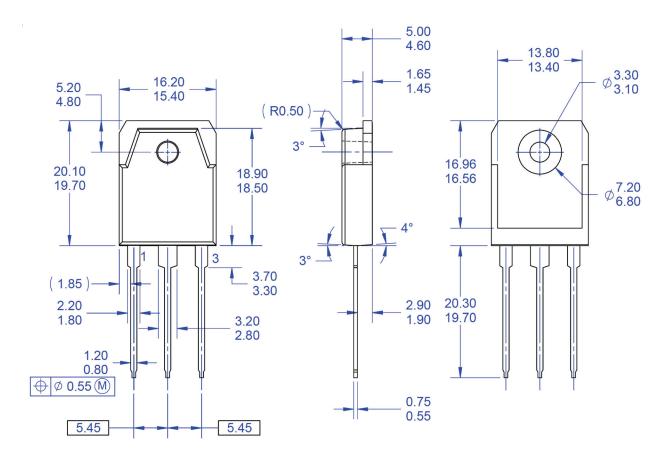
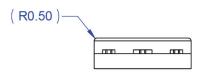


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**





NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
  C) DIMENSION AND TOLERANCING PER
- ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS. DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

### Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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